Power Discrete Market & Supply Chain

1901-2012年期間表面溫度的改變 Observed change in surface temperature 1901-2012



Paris Climate Agreement



(a) Holding the increase in the global average temperature to well below 2 °C above pre-industrial levels and to pursue efforts to limit the temperature increase to 1.5 °C above pre-industrial levels, recognizing that this would significantly reduce the risks and impacts of climate change;

(b) Increasing the ability to adapt to the adverse impacts of climate change and foster climate resilience and low greenhouse gas emissions development, in a manner that does not threaten food production;

(c) Making finance flows consistent with a pathway towards low greenhouse gas emissions and climateresilient development.

Reducing CO_2 Improve energy efficiency



新能源 再生能源



使用效率 轉化效率

Power Discrete Market

Continue Growing

USD B\$



- 2016-2022 12.3B\$ to 19.5B\$
 <Chlue Research>
- Market share 2016 APAC hold 39.8%, China is the fast growing
- Driven by Automotive, Industry 4.0, New energy

Power Discrete Market Size by Segment







Source: Infineon



Power Discrete Types

Power Semiconductor

Power Discrete				Power IC		Power Module
Thryristor 閘流體	Rectifier 整流器	Diode 二極體	Transistor 電晶體 (MOSFET, IGBT, BJT)	Power Management IC (Regulator, Switch IC, Driver IC, PMIC, Supervisor/Smart IC)	Motion Control IC	Automobile applications with Integrated passive components

Structure of Various Power Discrete



Comparison of Power Discretes

Power Capacity in kVA



Source: YOLE

Evolution of Power Discrete



Source: YOLE

Process challenge

Middle End Thinning Wafer Process
Stress
High Dose Implantation (IGBT)
Laser Anneal (IGBT) Back End Heat Dissipation Thermal and Mechanical Stress Control

Technique Evolution -ROHM

Products Technical Support Applications Sales Buy or Sample

ROHM

Global - English

New 650V IGBTs Deliver Class-Leading Efficiency with Soft Switching

ROHM has announced the availability of 2 new types of 650V IGBTs that combine class-leading low conduction loss with high-speed switching characteristics. This makes them ideal for power conversion in generalpurpose inverters and converters for consumer appliances, such as ACs and IH (Induction Heaters), as well as industrial equipment, including power conditioners, welding machines, and UPS (Uninterrupted Power Supplies). A total of 21 models are offered, consisting of the RGTV series, which features short-circuit tolerance, and the RGW series that delivers fast switching speed.



In recent years, the emergence of IoT has caused an exponential growth in the volume of data generated, bringing about a need to improve the functionality and capacity of data centers. However, as the number of servers

and UPS essential to ensuring stable operation of the main power supply continues to rise, it becomes increasingly difficult to reduce power consumption. In addition, in high-power applications that utilize IGBTs there is a need to maintain reliability by simplifying measures against overshoot during switching, which can lead to device failure or malfunction.



These two new series adopt thin wafer technology that reduces wafer thickness by 15% over conventional products and an original structure featuring a refined cell design to provide the industry's lowest conduction loss (VCE(sat)=1.5V) with fast switching characteristics (tf=30 to 40ns).

Technique Evolution - First Tier IDM



IGBT Thinning Roadmap



◎ IGBT 400V ◎ IGBT600V ◎ IGBT 1200V

Power Discrete Package Trend



Source: YOLE

Power Loss Impact by Package



Source: https://epc-co.com/epc/DesignSupport/Chip-ScalePackaging.aspx

Power Discrete Supply Chain

Criteria of Supply Chain

Reliability Stable > High Yield Rate Verifiable Long term MP Experiance

Process Services Vender

FEOL

tsmc
VIA
UMC
Maxchip etc..

中段 PSI、XinTech、 Chipbond、mmec etc..

BEOL GEM LingSen etc

Outsourcing Flow

Differentiation/ Profit 2X2 Matrix



Division VS Integration



